

EV318283583

8/13/03

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-2382		PRIORITY SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Micron Technology, Inc.			
					PRIORITY FILING DATE 10/19/99		PRIORITY GROUP Unknown	
U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
✓	AA	4,341,662	7/82	Pfefferle				
	AB	4,431,750	2/84	McGinnis et al.				
	AC	4,714,693	12/87	Targos				
	AD	3,975,304	8/76	della Porta et al.				
	AE	3,856,709	12/74	Porta et al.				
	AF	5,525,570	6/96	Chakraborty et al.				
	AG	5,330,700	7/94	Soukup et al.				
✓	AH	4,719,442	1/88	Bohars et al.				
FOREIGN PATENT DOCUMENTS								
	Document Number	Date	Country	Class	Subclass	Translation		
						Yes	No	
✓	AI	9-082666	Japan					
✓	AJ	0 415 751 A1	EPO					
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
✓	AK	Ju-Hong Kwan et al.; "Characterization of Pt Thin Films Deposited by Metallorganic Chemical Vapor Deposition for Ferroelectric Bottom Electrodes"; J. Electrochem. Soc., Vol. 144, No. 8, August 1997; pp. 2848-2854						
✓	AL	M. Ito et al.; "Rugged surface polycrystalline silicon film deposition and its application in a stacked dynamic random access memory capacitor electrode"; J. Vac. Sci. Technol. B 14(2), March/April 1996; pp. 751-756						
	AM							
	AN							
	AO							
EXAMINER				DATE CONSIDERED				
HUNG VU				03/17/05				
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. M122-2382		PRIORITY SERIAL NO. Filed Herewith	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Micron Technology, Inc.			
					PRIORITY FILING DATE 10/19/99		PRIORITY GROUP Unknown	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
✓	AA	5,639,685	6/97	Zahurak et al.				
	AB	5,917,213	6/99	Iyer et al.				
	AC	5,874,364	2/99	Nakabayashi et al.				
	AD	5,053,917	10/91	Miyasaka et al.				
	AE	5,208,479	5/93	Mathews et al.				
	AF	5,783,716	7/98	Baum et al.				
	AG	5,796,648	8/98	Kawakubo et al.				
✓	AH	5,763,286	6/98	Figura et al.				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
✓	AI	5-67730		Japan				
✓	AJ	0 855 738 A2		EPO				
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AK							
	AL							
	AM							
	AN							
EXAMINER HUNG JU					DATE CONSIDERED 03/17/05			
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					PRIORITY FILING DATE 10/19/99		PRIORITY GROUP Unknown	
U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
✓	AA	5,320,978	6/94	Hsu				
	AB	6,033,953	3/00	Aoki et al.				
	AC	5,990,559	11/99	Marsh				
	AD	4,425,261	1/84	Stenius et al.				
	AE	6,175,129	1/01	Liu et al.				
	AF	6,010,744	1/00	Buskirk et al.				
	AG	5,555,486	9/96	Kington et al.				
	AH	6,232,629	5/01	Nakamura				
✓	AI	5,635,420	6/97	Nishioka				
	AJ							
FOREIGN PATENT DOCUMENTS								
	Document Number	Date	Country	Class	Subclass	Translation		
						Yes	No	
✓	AK	JP 9051079	2/18/97	Japan				
	AL	JP 8017939	6/3/03	Japan				
	AM	JP 10173149	6/26/98	Japan				
✓	AN	JP 10180098	7/7/98	Japan				
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AQ							
	AR							
	AS							
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-2382		SERIAL NO. 10/642,454	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Eugene P. Marsh			
					FILING DATE August 13, 2003		GROUP 2811	
U.S. PATENT DOCUMENTS								
Examiner's Initials	AA	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA							
	AB							
	AC							
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ						X	
	AK							
	AL							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)								
✓ H	AM	Nasu, T. et al., "Study of Pt Bottom Electrodes Using High-Temperature Sputtering for Ferroelectric Memories with SrBi ₂ Ta ₂ O ₉ (SBTO) Film", Jpn. J. Appl. Phys. Vol. 37, Part 1, No. 7 (July 1998), pp. 4144-4148.						
	AN							
	AO							
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1 OF 1

